

**FAST SWITCHING DIODE**
**FEATURES**

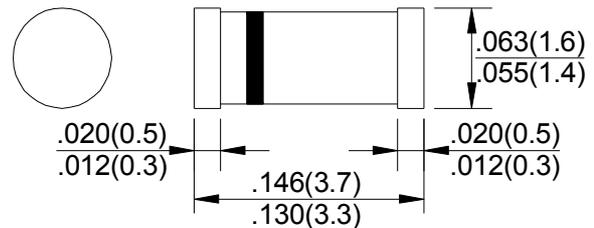
- High reliability
- High conductance
- Fast switching speed ( $t_{rr} \leq 4ns$ )

**APPLICATIONS**

- For general purpose switching applications

**CONSTRUCTION**

- Silicon epitaxial planar

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Dimensions in inches and (millimeters)

**ABSOLUTE MAXIMUM RATING** ( $T_J=25^\circ C$ )

Parameter	Test Conditions	Symbol	Value	Unit
Non repetitive peak reverse voltage		$V_{RM}$	100	V
Repetitive peak reverse voltage		$V_{RRM}$	75	V
Working peak reverse voltage		$V_{RWM}$	75	V
DC blocking voltage		$V_R$	75	V
RMS reverse voltage		$V_{R(RMS)}$	53	V
Forward current		$I_F$	300	mA
Average rectified current	Half wave rectification with resistive load and $f > 50MHz$	$I_{FAV}$	200	mA
Non repetitive peak forward surge current	$t=1s$	$I_{FSM}$	1	A
	$t=1\mu s$	$I_{FSM}$	4	A
Power dissipation	$l=4mm$ $T_L=25^\circ C$	$P_d$	500	mW
Storage temperature range		$T_{stg}$	-65 ~ +175	$^\circ C$

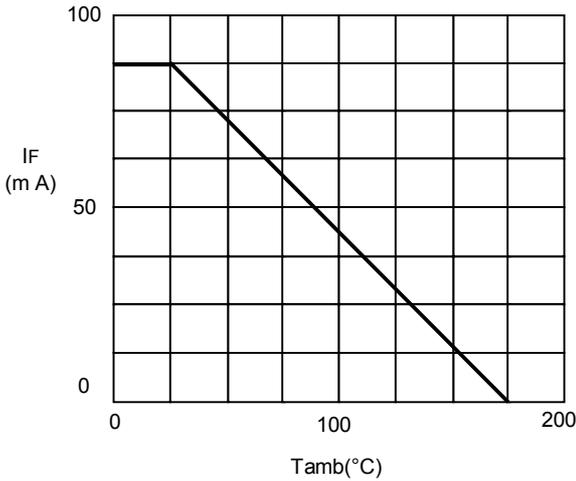
**MAXIMUM THERMAL RESISTANCE** ( $T_J=25^\circ C$ )

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	$l=4mm$ $T_L=constant$	$R_{thJA}$	300	K/W

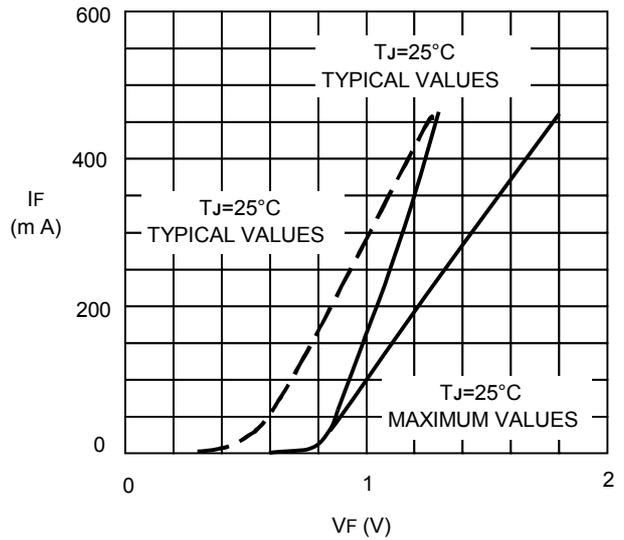
**ELECTRICAL CHARACTERISTICS**  $T_J=25^\circ C$ 

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=10mA$	$V_F$			1	V
Peak reverse current	$V_R=20V$	$I_R$			25	nA
	$V_R=20V, T_J=150^\circ C$	$I_R$			50	$\mu A$
	$V_R=75V$	$I_R$			5	$\mu A$
Breakdown voltage	$I_R=100\mu A$	$V_R$	100			V
Diode capacitance	$V_R=0, f=1MHz$	$C_D$			4	pF
Reverse recovery time	$I_F=10mA$ to $I_R=1mA, V_R=6V, R_L=100\Omega$	$t_{rr}$			4	ns

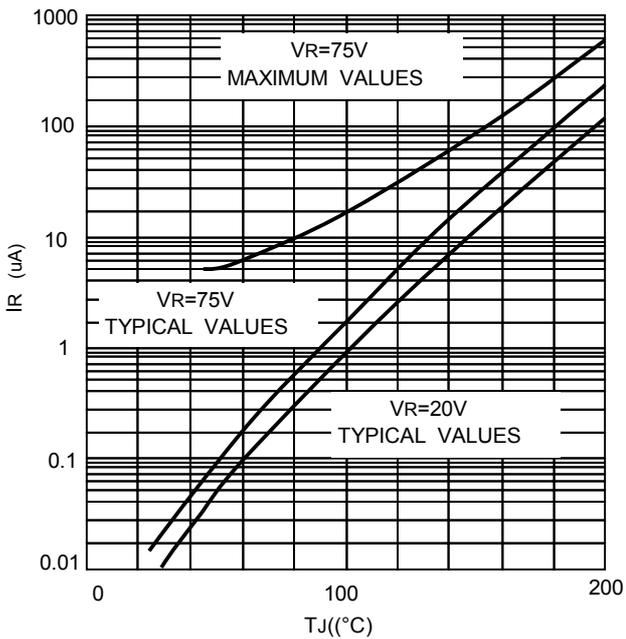
**FIG. 1 - MAXIMUM PERMISSIBLE CONTINUOUS FORWARD CURRENT VS. AMBIENT TEMPERATURE**



**FIG. 2 - FORWARD CURRENT VS. FORWARD VOLTAGE**



**FIG. 3 - REVERSE CURRENT VS. JUNCTION TEMPERATURE**



**FIG. 4 - DIODE CAPACITANCE VS. REVERSE VOLTAGE (TYPICAL VALUES)**

